

## FQP18N20V2/FQPF18N20V2

### 200V N-Channel MOSFET

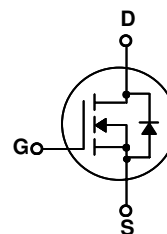
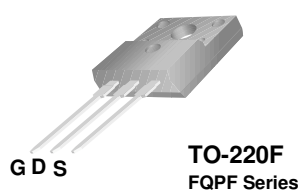
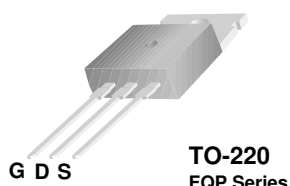
#### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as automotive, high efficiency switching for DC/DC converters, and DC motor control.

#### Features

- 18A, 200V,  $R_{DS(on)} = 0.14\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 20 nC)
- Low Crss ( typical 25 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FQP18N20V2	FQPF18N20V2	Units
V <sub>DSS</sub>	Drain-Source Voltage	200		V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	18	18	A
		11.9	11.9	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	72	72	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30		V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	340		mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	18		A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	12.3		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.5		V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	123	40	W
		0.99	0.32	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150		°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

#### Thermal Characteristics

Symbol	Parameter	FQP18N20V2	FQPF18N20V2	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	1.01	3.1	°C/W
R <sub>θCS</sub>	Thermal Resistance, Case-to-Sink	0.5	--	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.25	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	--	0.12	0.14	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 9\text{ A}$ (Note 4)	--	11	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	830	1080	pF
$C_{oss}$	Output Capacitance		--	200	260	pF
$C_{riss}$	Reverse Transfer Capacitance		--	25	33	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	70	--	pF
$C_{oss\text{ eff.}}$	Effective Output Capacitance	$V_{DS} = 0\text{V to } 160\text{ V}, V_{GS} = 0\text{ V}$	--	135	--	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 18\text{ A},$ $R_G = 25\ \Omega$	--	16	40	ns	
$t_r$	Turn-On Rise Time		--	133	275	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	38	85	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	62	135	ns
$Q_g$	Total Gate Charge		$V_{DS} = 160\text{ V}, I_D = 18\text{ A},$	--	20	26	nC
$Q_{gs}$	Gate-Source Charge		$V_{GS} = 10\text{ V}$	--	5.6	--	nC
$Q_{gd}$	Gate-Drain Charge	(Note 4, 5)	--	10	--	nC	

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	18	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	72	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 18\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 18\text{ A},$	--	158	--	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	1.0	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 1.58\text{mH}, I_{AS} = 18\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 18\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

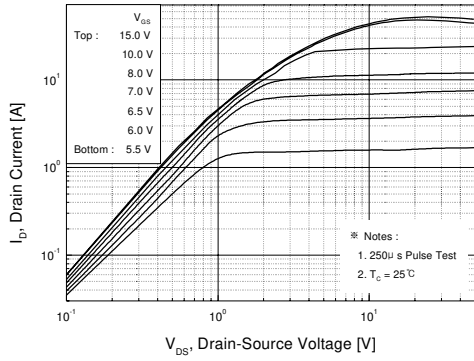


Figure 1. On-Region Characteristics

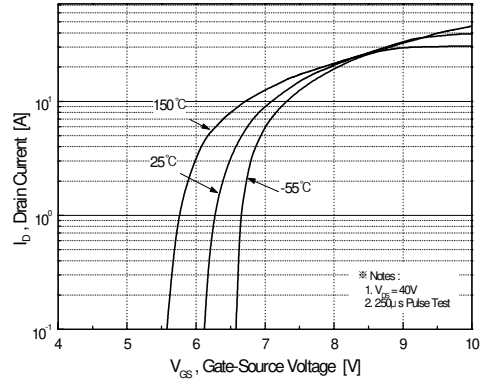


Figure 2. Transfer Characteristics

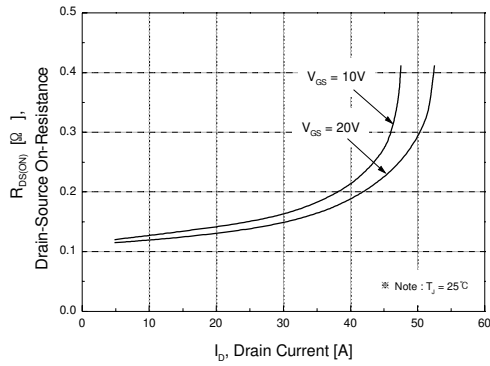


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

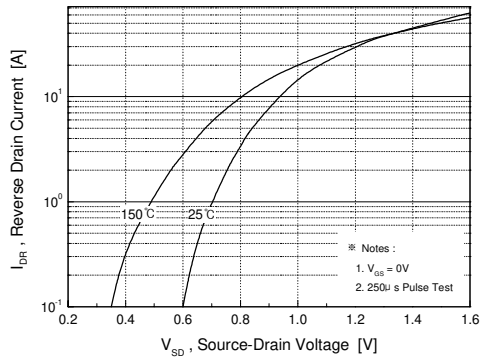


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

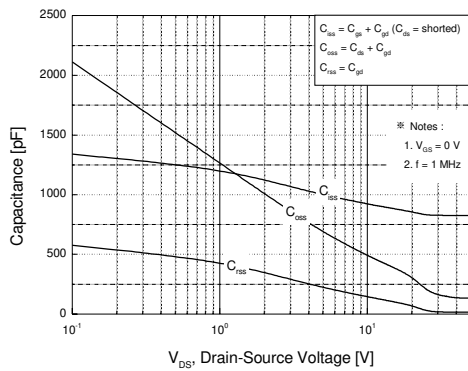


Figure 5. Capacitance Characteristics

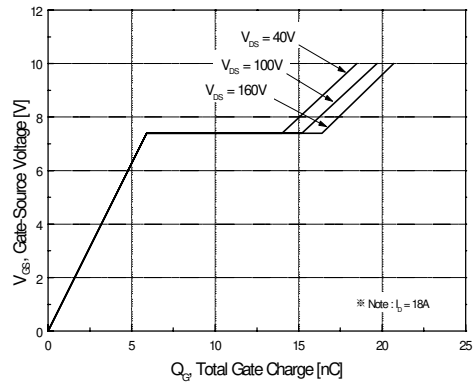
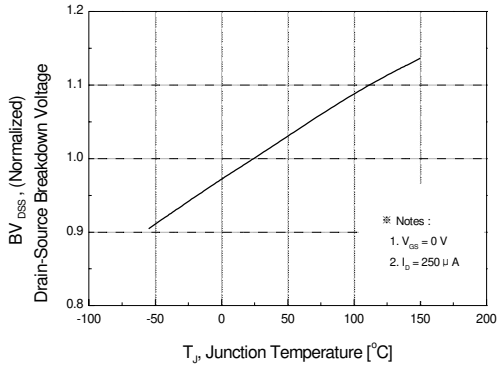
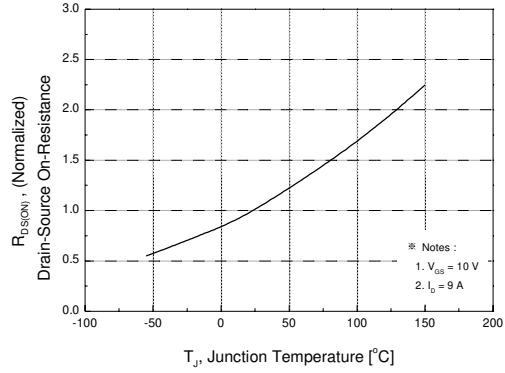


Figure 6. Gate Charge Characteristics

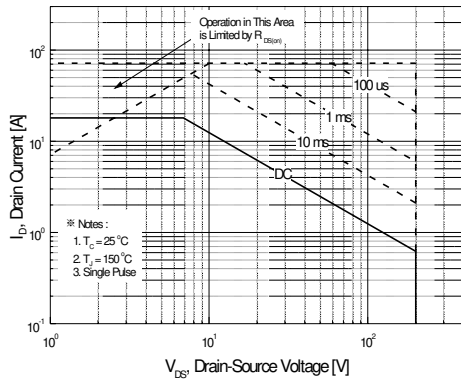
**Typical Characteristics** (Continued)



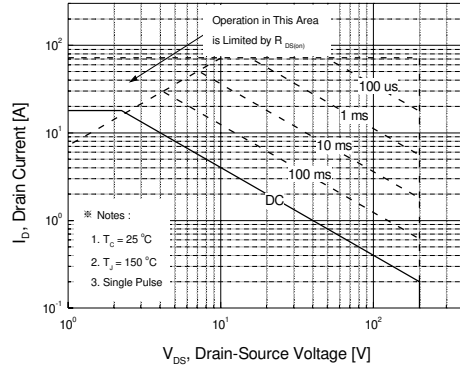
**Figure 7. Breakdown Voltage Variation vs. Temperature**



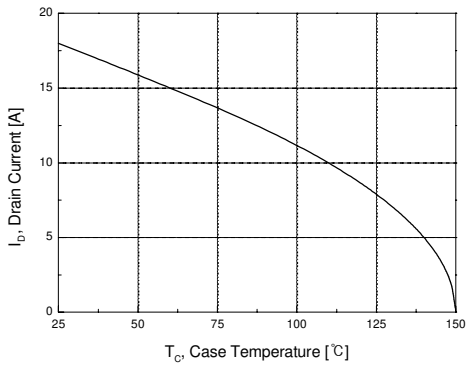
**Figure 8. On-Resistance Variation**



**Figure 9-1. Maximum Safe Operating Area for FQP18N20V2**

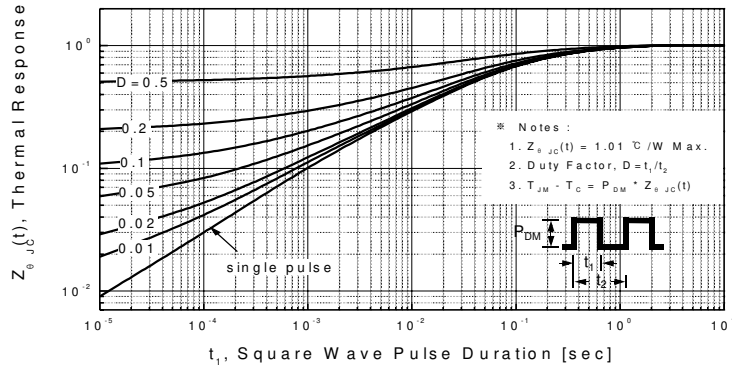


**Figure 9-2. Maximum Safe Operating Area for FQPF18N20V2**

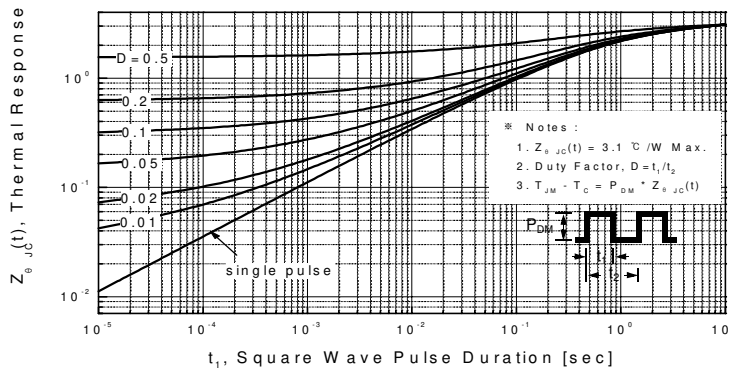


**Figure 10. Maximum Drain Current vs. Case Temperature**

**Typical Characteristics** (Continued)

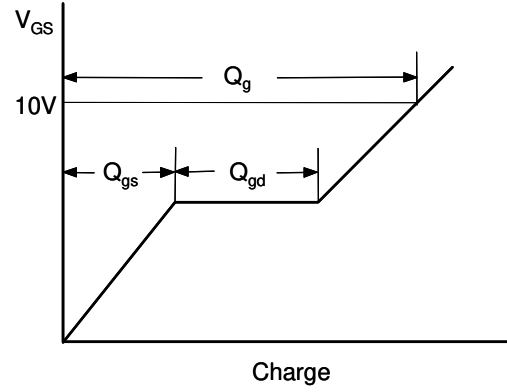
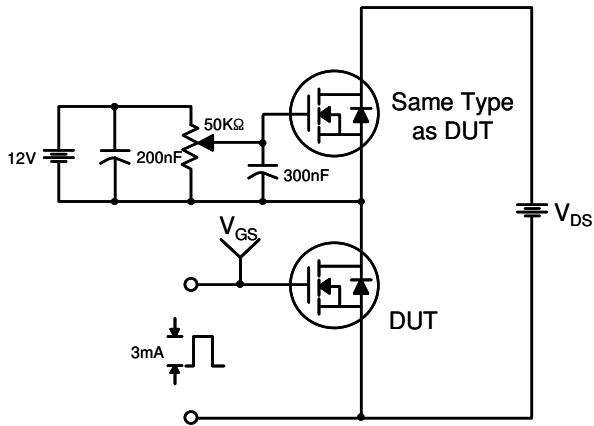


**Figure 11-1. Transient Thermal Response Curve for FQP18N20V2**

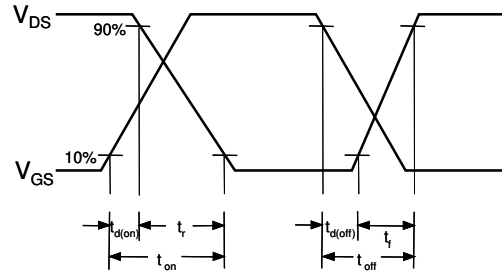
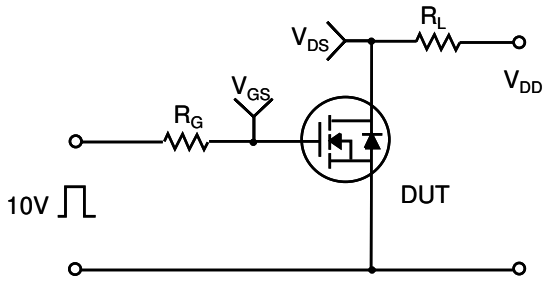


**Figure 11-2. Transient Thermal Response Curve for FQPF18N20V2**

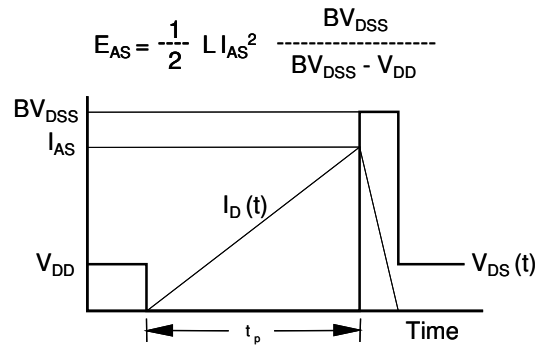
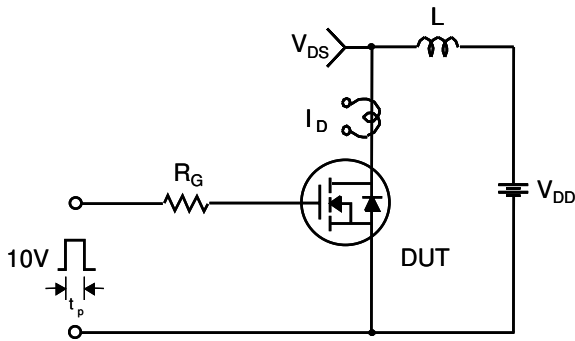
**Gate Charge Test Circuit & Waveform**



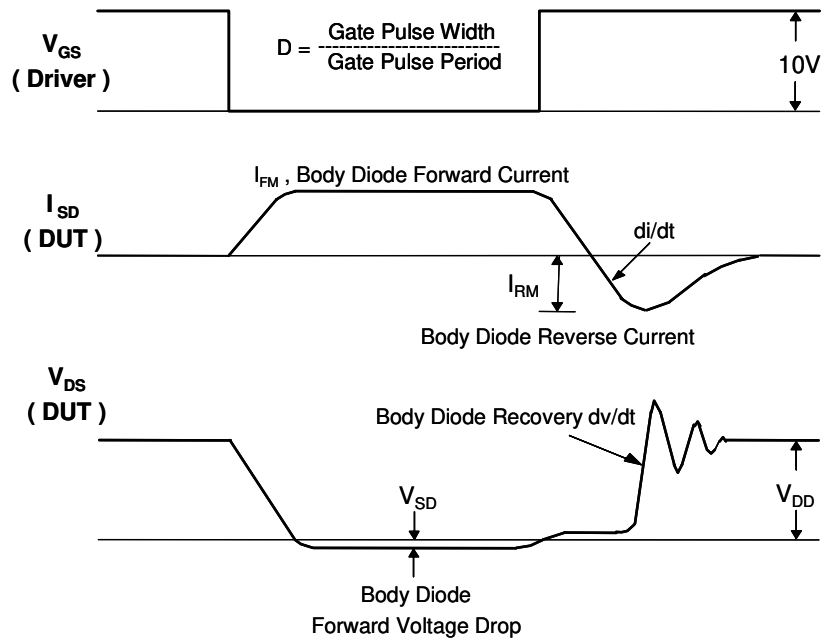
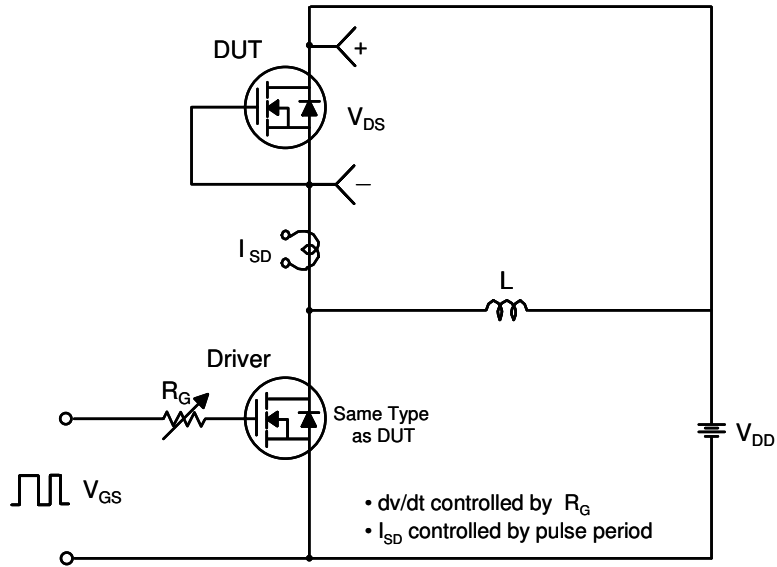
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

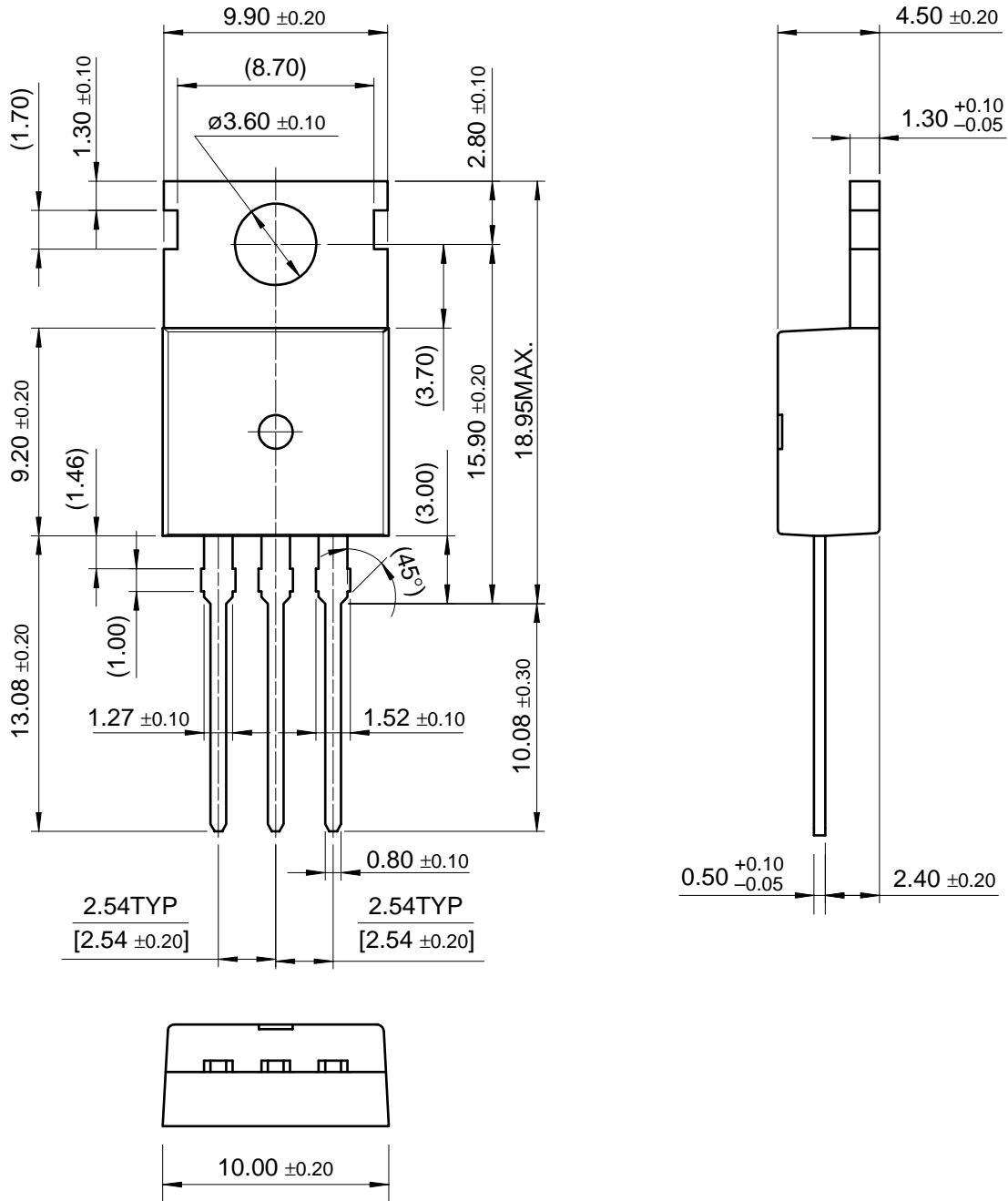


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## TO-220



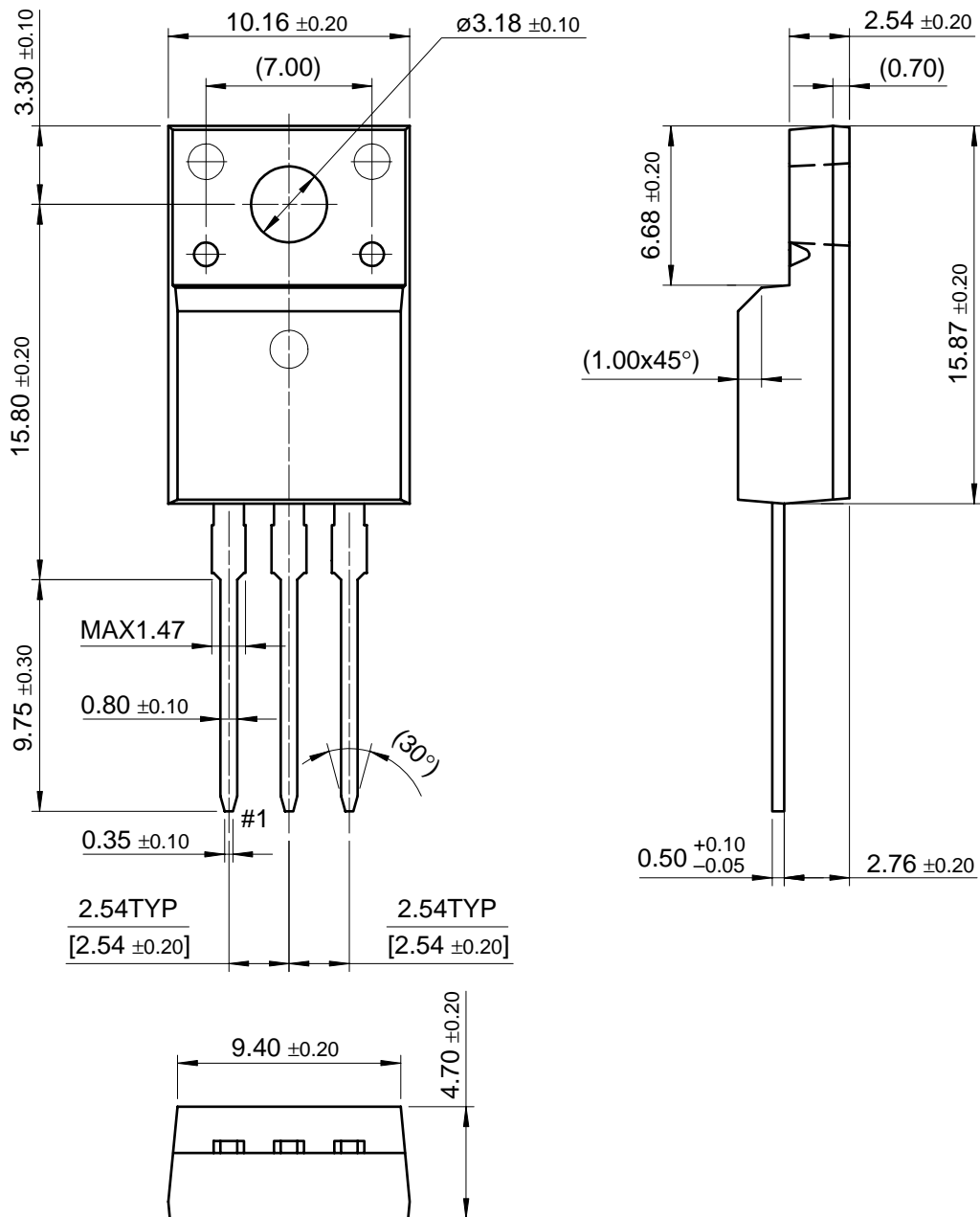
Dimensions in Millimeters

FQP18N20V2/FQP18N20V2



Package Dimensions (Continued)

TO-220F



Dimensions in Millimeters

FQP18N20V2/FQP18N20V2

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CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
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